Analog Power

Dual N-Channel Logical Level MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

	PRODUCTSUMMARY				
	$V_{DS}(V)$	$r_{DS(on)}\left(OHM\right)$	I _D (A)		
	20	$0.012 @ V_{GS} = 4.5 V$	9.2		
		$0.014 @ V_{GS} = 2.5V$	8.5		
\		DFN 3x3) D		

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Top View

- $\begin{tabular}{ll} \textbf{Low} & r_{DS(on)} & provides & higher efficiency & and \\ extends & battery & life \\ \end{tabular}$
- Low thermal impedance copper leadframe
 DFN 3x3 saves board space

 COMPLIANT
 HALOGEN
 FREE
- Fast switching speed
- High performance trench technology



RoHS

COMPLIANT

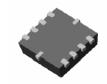
S1 □

G1 <u></u> 2

S2 🔲 3

G2 🔲 4





MOSFET

N-Channel

MOSFET

AMCC924NE

ESD Protected 2000V

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Maximum	Units				
Drain-Source Voltage		V_{DS}	20	V			
Gate-Source Voltage	V_{GS}	±8	V				
Continuous Drain Current ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	I _D	9.2	A			
Continuous Drain Current	$T_A=70^{\circ}C$	ър	7.5				
Pulsed Drain Current ^b	I_{DM}	±40					
Continuous Source Current (Diode Conduction) ^a		I_S	1.5	A			
Power Dissipation ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	\mathbf{p}_{D}	1.5	W			
1 Ower Dissipation	$T_A=70^{\circ}C$	1 D	1.0	,,			
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Тур	Max				
M . I	t <= 10 sec	R_{thJA}	72	83	°C/W		
Maximum Junction-to-Ambient ^a	Steady State		100	120			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

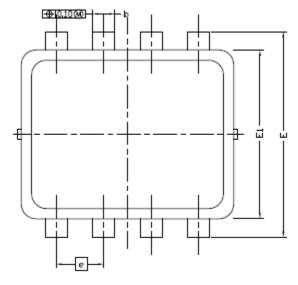
SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Conditions				Unit	
	S J 222 S J		Min	in Typ Max			
Static							
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}$, $I_{D} = 250 \text{ uA}$	0.3			V	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			±10	μA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ	
Zero Gate Voltage Brain Current	-DSS	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	μΑ	
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			A	
Drain-Source On-Resistance ^A	r _{DS(on)}	VGS = 4.5 V, ID = 2 A			0.012	Ω	
Drain-Gource On-Acsistance		$V_{GS} = 2.5 \text{ V}, \text{ ID} = 2 \text{ A}$			0.014		
Forward Tranconductance ^A	g_{fs}	$V_{DS} = 10 \text{ V}, I_D = 2 \text{ A}$		25		S	
Diode Forward Voltage ^A	V_{SD}	$I_S = 2 A, V_{GS} = 0 V$		0.89		V	
Dynamic ^b							
Total Gate Charge	Q_{g}			13.4			
Gate-Source Charge	Q_{gs}	V_{DS} =10V, V_{GS} =4.5V, I_{D} =2A		0.9		nC	
Gate-Drain Charge Q _{gd}				2.0			
Turn-On Delay Time	$t_{d(on)}$			18			
Rise Time	t _r	$V_{DD} = 10V, V_{GS} = 4.5V, I_{D} = 1A$,		25		nS	
Turn-Off Delay Time	$t_{d(off)}$	$R_{\text{GEN}} = 10\Omega$		50] 113	
Fall-Time	t_{f}			25		Ī	

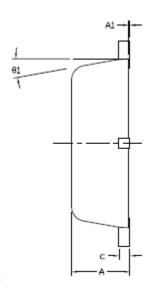
Notes

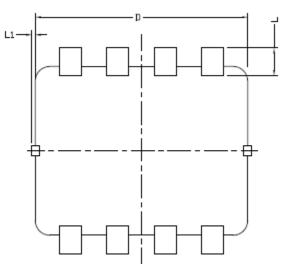
- a. Pulse test: $PW \le 300$ us duty cycle $\le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Package Information







DIM.	MILLIMETERS			INCHES			
DIN.	MIN	M	MAX	MIN	M	MAX	
Α	0.700	0.80	0.900	0.0276	0.0315	0.0354	
A1	0.00		0.05	0.000	İ	0.002	
О	0,24	0'30	0,35	0,009	0,012	0,014	
0	0.08	0.152	0.25	0.003	0.006	0.010	
D	2	2.90 BS	С	0.114 BSC			
Ε	a	2.80 BS	С	0.110 BSC			
E1	2.30 BSC			0.091 BSC			
6	0.65 BSC			0.05e B2C			
L	0.20	0.375	0.450	0.008	0.0148	0.0177	
L1	0		0.100	0		0.004	
91	0*	10°	12*	0*	10*	12*	